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Cora M. Utley
Cora M. Utley

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of Christopher L. Chua et al.

Group Art Unit: 2828

Application No.: 09/933,960

Examiner: James A. Menefee

Filed: August 20, 2001

Confirmation No.: 9309

For: METHOD AND STRUCTURE FOR ELIMINATING POLARIZATION INSTABILITY IN Laterally - OXIDIZED VCSELS

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Application No. 09/933,960

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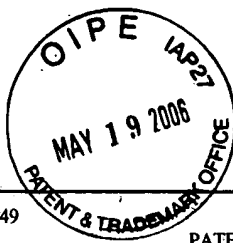
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| | APPLICANT(S) Robert L. THORNTON | | | |
| | FILING DATE August 20, 2001 | | GROUP 2828 | |

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